



MOC205M, MOC206M, MOC207M, MOC208M Small Outline Optocouplers Transistor Output

Features

- U.L. recognized (File #E90700, Volume 2)
- VDE recognized (File #136616) (add option "V" for VDE approval, i.e, MOC205VM)
- Closely matched current transfer ratios
- Convenient plastic SOIC-8 surface mountable package style
- Minimum BV_{CEO} of 70 Volts guaranteed
- Standard SOIC-8 footprint, with 0.050" lead spacing
- Compatible with dual wave, vapor phase and IR reflow soldering
- High input-output isolation of 2500 V_{AC(rms)} guaranteed

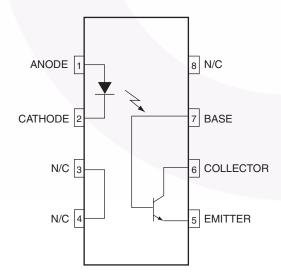
Applications

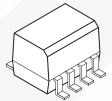
- Feedback control circuits
- Interfacing and coupling systems of different potentials and impedances
- General purpose switching circuits
- Monitor and detection circuits

Description

These devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector, in a surface mountable, small outline, plastic package. They are ideally suited for high density applications, and eliminate the need for throughthe-board mounting.

Schematic





Absolute Maximum Ratings (T_A = 25°C Unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Rating	Value	Unit
EMITTER			
I _F	Forward Current – Continuous	60	mA
I _F (pk)	Forward Current – Peak (PW = 100µs, 120pps)	1.0	А
V _R	Reverse Voltage	6.0	V
P _D	LED Power Dissipation @ T _A = 25°C	90	mW
	Derate above 25°C	0.8	mW/°C
DETECTOR			
V _{CEO}	Collector-Emitter Voltage	70	V
V _{ECO}	Emitter-Collector Voltage	7.0	V
V _{CBO}	Collector-Base Voltage	70	V
I _C	Collector Current-Continuous	150	mA
P _D	Detector Power Dissipation @ T _A = 25°C	150	mW
	Derate above 25°C	1.76	mW/°C
TOTAL DEVICE			
V_{ISO}	Input-Output Isolation Voltage (f = 60Hz, t = 1 min.) $^{(1)(2)(3)}$	2500	Vac(rms)
P _D	Total Device Power Dissipation @ T _A = 25°C	250	mW
	Derate above 25°C	2.94	mW/°C
T _A	Ambient Operating Temperature Range	-40 to +100	°C
T _{stg}	Storage Temperature Range	-40 to +150	°C

Notes:

- 1. Isolation Surge Voltage, V_{ISO}, is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.
- 3. V_{ISO} rating of 2500 $V_{AC(rms)}$ for t = 1 min. is equivalent to a rating of 3,000 $V_{AC(rms)}$ for t = 1 sec.

Electrical Characteristics ($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.*	Max.	Unit
EMITTER						
V _F	Input Forward Voltage	I _F = 10mA		1.15	1.5	V
I _R	Reverse Leakage Current	V _R = 6.0V		0.001	100	μΑ
C _{IN}	Input Capacitance			18		pF
DETECTO	OR .		•	1		1
I _{CEO1}	Collector-Emitter Dark Current	V _{CE} = 10V, T _A = 25°C V _{CE} = 10V, T _A = 100°C		1.0 1.0	50	nA μA
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \mu A$	70	100		V
BV _{ECO}	Emitter-Collector Breakdown Voltage	I _E = 100μA	7.0	10		V
C _{CE}	Collector-Emitter Capacitance	f = 1.0 MHz, V _{CE} = 0		7.0		pF
COUPLE	D					
CTR	Collector-Output Current ⁽⁴⁾ MOC205M MOC206M MOC207M MOC208M1	I _F = 10mA, V _{CE} = 10V	40 63 100 40		80 125 200 125	%
V _{ISO}	Isolation Surge Voltage ⁽¹⁾⁽²⁾⁽³⁾	f = 60 Hz AC Peak, t = 1 min.	2500			Vac(rms)
R _{ISO}	Isolation Resistance ⁽²⁾	V = 500V	10 ¹¹	\		Ω
V _{CE (sat)}	Collector-Emitter Saturation Voltage	$I_C = 2mA$, $I_F = 10mA$			0.4	V
C _{ISO}	Isolation Capacitance ⁽²⁾	V = 0V, f = 1MHz		0.2		pF
t _{on}	Turn-On Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{ V},$ $R_L = 100 \Omega \text{ (Fig. 6)}$		7.5		μs
t _{off}	Turn-Off Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega \text{ (Fig. 6)}$		5.7		μs
t _r	Rise Time	$I_C = 2.0 \text{mA}, V_{CC} = 10 \text{V},$ $R_L = 100 \Omega \text{ (Fig. 6)}$		3.2		μs
t _f	Fall Time	$I_C = 2.0 \text{ mA}, V_{CC} = 10 \text{ V},$ $R_L = 100\Omega \text{ (Fig. 6)}$		4.7		μs

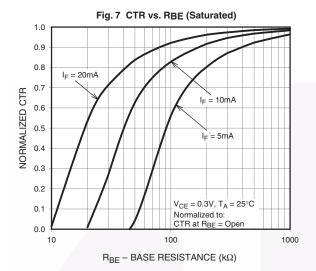
^{*}Typical values at T_A = 25°C

Notes:

- 1. Isolation Surge Voltage, V_{ISO} , is an internal device dielectric breakdown rating.
- 2. For this test, Pins 1 and 2 are common and Pins 5, 6 and 7 are common.
- 3. V_{ISO} rating of 2500 $V_{AC(rms)}$ for t = 1 min. is equivalent to a rating of 3,000 $V_{AC(rms)}$ for t = 1 sec.
- 4. Current Transfer Ratio (CTR) = $I_C/I_F \times 100\%$.

Typical Performance Curves Fig. 1 LED Forward Voltage vs. Forward Current Fig. 2 Output Curent vs. Input Current $_{\rm l_{\rm c}}$ – OUTPUT COLLECTOR CURRENT (NORMALIZED) 1.7 V_F - FORWARD VOLTAGE (V) V_{CE} = 5V NORMALIZED TO I_F = 10mA 1.5 1.3 1.0 100 I_F – LED FORWARD CURRENT (mA) 0.1 10 100 I_E – LED INPUT CURRENT (mA) Fig. 3 Output Current vs. Ambient Temperature Fig. 4 Output Current vs. Collector-Emitter Voltage CURRENT (NORMALIZED) - OUTPUT COLLECTOR CURRENT (NORMALIZED) 1.2 1.0 OUTPUT COLLECTOR 0.8 0.6 0.4 0.2 $I_F = 10$ mA NORMALIZED TO $V_{CE} = 5$ V NORMALIZED TO TA = 25°C -80 -60 -40 0 100 0 V_{CE} – COLLECTOR-EMITTER VOLTAGE (V) T_A – AMBIENT TEMPERATURE (°C) Fig. 5 Dark Current vs. Ambient Temperature Fig. 6 CTR vs. RBE (Unsaturated) 10000 1.0 _{OEO} - COLLECTOR -EMITTER DARK CURRENT (nA) 0.9 V_{CE} = 10V 1000 $I_F = 20 \text{mA}$ 0.8 0.7 100 0.6 NORMALIZED CTR $l_F = 5mA$ 10 0.4 0.3 0.2 $V_{CE} = 5V, T_A = 25^{\circ}C$ Normalized to: 0.1 CTR at R_{BE} = Open 0.0 0.1 10 1000 20 40 $R_{\mbox{\footnotesize{BE}}}$ -BASE RESISTANCE (k Ω) T_A – AMBIENT TEMPERATURE (°C)

Typical Performance Curves (Continued)



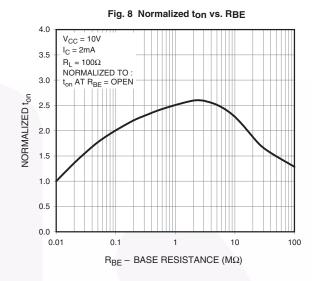


Fig. 9 Normalized toff vs. RBE 1.6 V_{CC} = 10V $I_C = 2mA$ 1.4 $R_L = 100\Omega$ NORMALIZED TO : t_{off} AT R_{BE} = OPEN NORMALIZED toff 1.0 0.8 0.6 0.2 0.0 10 0.01 100 R_{BE} – BASE RESISTANCE (M Ω)

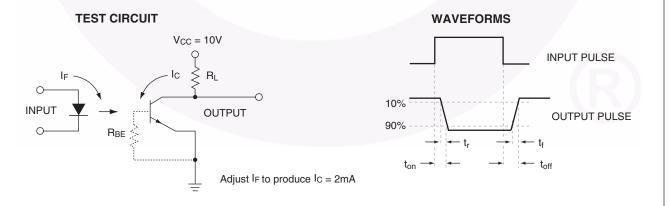
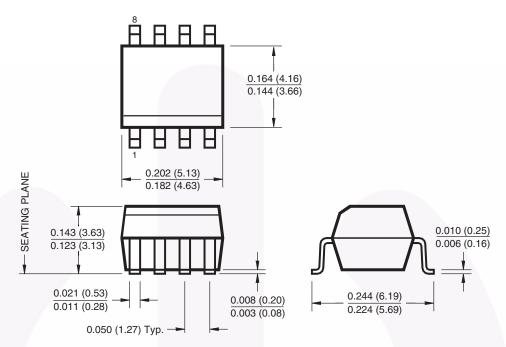


Figure 10. Switching Time Test Circuit and Waveforms

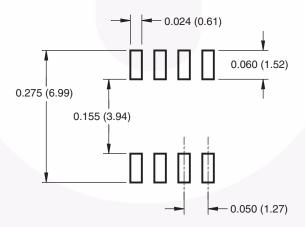
Package Dimensions

8-pin SOIC Surface Mount



Lead Coplanarity: 0.004 (0.10) MAX

Recommended Pad Layout



Dimensions in inches (mm).

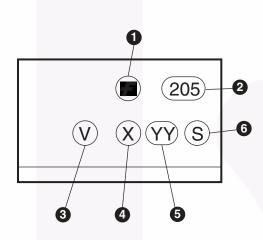
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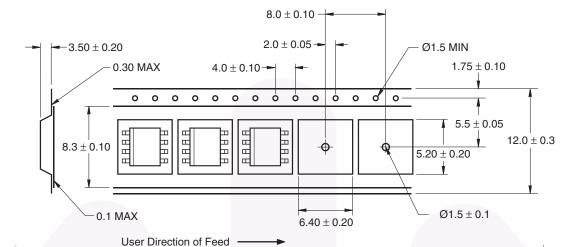
Option	Order Entry Identifier	Description
V	V	VDE 0884
R2	R2	Tape and reel (2500 units per reel)
R2V	R2V	VDE 0884, Tape and reel (2500 units per reel)

Marking Information



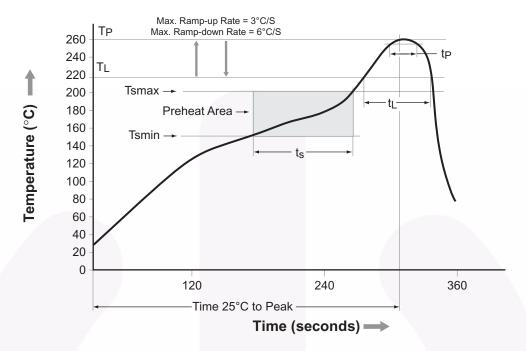
Defini	tions	
1	Fairchild logo	
2	Device number	
3	VDE mark (Note: Only appears on parts ordered with VDE option – See order entry table)	
4	One digit year code, e.g., '8'	
5	Two digit work week ranging from '01' to '53'	
6	Assembly package code	

Carrier Tape Specifications



Dimensions in mm

Reflow Profile



Profile Freature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (t _S) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60-150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of 260°C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max.
Time 25°C to Peak Temperature	8 minutes max.





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